



## PATENT ABSTRACTS OF JAPAN

(11) Publication number: **2002026121 A**(43) Date of publication of application: **25.01.02**

(51) Int. Cl.

**H01L 21/768**  
**H01L 21/316**(21) Application number: **2000199737**(22) Date of filing: **30.06.00**(71) Applicant: **TOKYO ELECTRON LTD**(72) Inventor:  
**MAEKAWA KAORU**  
**NAGAI HIROYUKI**  
**INASAWA KOICHIRO**  
**SUEMASA TOMOKI**

(54) **SEMICONDUCTOR DEVICE AND METHOD OF  
MANUFACTURING THE SAME, AND METHOD  
OF FORMING INSULATION FILM**

(57) Abstract:

PROBLEM TO BE SOLVED: To increase the resistance with respect to various chemicals and plasma used in semiconductor manufacturing processes by improving the adhesiveness of a low-density film having low permittivity.

SOLUTION: The surface of the low-density film, having a low permittivity, is plasma-treated to form a very fine surface modified layer.

COPYRIGHT: (C)2002,JPO

